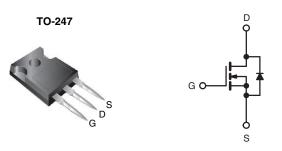


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# **Power MOSFET**



N-Channel MOSFET

PRODUCT SUMMARY			
V <sub>DS</sub> (V)	500		
$R_{DS(on)}(\Omega)$	V <sub>GS</sub> = 10 V 0.27		
Q <sub>g</sub> (max.) (nC)	210		
Q <sub>gs</sub> (nC)	29		
Q <sub>gd</sub> (nC)	110		
Configuration	Single		

### **FEATURES**

- Dynamic dV/dt rating
- · Repetitive avalanche rated
- · Isolated central mounting hole
- · Fast switching
- · Ease of paralleling
- Simple drive requirements
- Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912"><u>www.vishay.com/doc?99912</u></a>

#### Note

\* This datasheet provides information about parts that are RoHS-compliant and / or parts that are non RoHS-compliant. For example, parts with lead (Pb) terminations are not RoHS-compliant. Please see the information / tables in this datasheet for details

### **DESCRIPTION**

Third generation Power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The TO-247 package is preferred for commercial-industrial applications where higher power levels preclude the use of TO-220 devices. The TO-247 is similar but superior to the earlier TO-218 package because its isolated mounting hole. It also provides greater creepage distances between pins to meet the requirements of most safety specifications.

ORDERING INFORMATION	
Package	TO-247
Lead (Pb)-free	IRFP460PbF

PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		V <sub>DS</sub>	500	V
Gate-source voltage		V <sub>GS</sub>	± 20	v
Continuous drain current	$V_{GS}$ at 10 V $T_{C} = 25 ^{\circ}C$ $T_{C} = 100 ^{\circ}C$		20	
Continuous drain current	$T_C = 100 ^{\circ}$ C	I <sub>D</sub>	13	Α
Pulsed drain current <sup>a</sup>		I <sub>DM</sub>	80	
Linear derating factor		2.2	W/°C	
Single pulse avalanche energy b	E <sub>AS</sub>	960	mJ	
Repetitive avalanche current <sup>a</sup>		I <sub>AR</sub>	20	Α
Repetitive avalanche energy <sup>a</sup>		E <sub>AR</sub>	28	mJ
Maximum power dissipation	T <sub>C</sub> = 25 °C	P <sub>D</sub>	280	W
Peak diode recovery dV/dt <sup>c</sup>	dV/dt	3.5	V/ns	
Operating junction and storage temperature range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C	
Soldering recommendations (peak temperature)		300 <sup>d</sup>		
Maratina Tarra			10	lbf ⋅ in
Mounting Torque	6-32 or M3 screw		1.1	N⋅m

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)
- b.  $V_{DD}$  = 50 V, starting  $T_J$  = 25 °C, L = 4.3 mH,  $R_G$  = 25  $\Omega$ ,  $I_{AS}$  = 20 A (see fig. 12)
- c.  $I_{SD} \le 20$  A,  $dI/dt \le 160$  A/ $\mu$ s,  $V_{DD} \le V_{DS}$ ,  $T_J \le 150$  °C
- d. 1.6 mm from case



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THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum junction-to-ambient	R <sub>thJA</sub>	-	40	
Case-to-sink, flat, greased surface	R <sub>thCS</sub>	0.24	-	°C/W
Maximum junction-to-case (drain)	R <sub>thJC</sub>	-	0.45	

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	$V_{DS}$	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA		500	-	-	V
V <sub>DS</sub> temperature coefficient	$\Delta V_{DS}/T_{J}$	Reference to 25	°C, I <sub>D</sub> = 1 mA	-	0.63	-	V/°C
Gate-source threshold voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}$ , $I_D = 2$	250 μA	2.0	-	4.0	V
Gate-source leakage	I <sub>GSS</sub>	$V_{GS} = \pm 20 \text{ V}$		-	-	± 100	nA
7		$V_{DS} = 500 \text{ V}, V_{GS}$	<sub>S</sub> = 0 V	-	-	25	
Zero gate voltage drain current	I <sub>DSS</sub>	$V_{DS} = 400 \text{ V}, V_{GS}$	<sub>S</sub> = 0 V, T <sub>J</sub> = 125 °C	-	-	250	μA
Drain-source on-state resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 12 A <sup>b</sup>	-	-	0.27	Ω
Forward transconductance	9 <sub>fs</sub>	$V_{DS} = 50 \text{ V}, I_{D} =$	12 A <sup>b</sup>	13	-	-	S
Dynamic							
Input capacitance	C <sub>iss</sub>	$V_{GS} = 0 V$		-	4200	-	
Output capacitance	C <sub>oss</sub>	$V_{DS} = 25 \text{ V},$		-	870	-	pF
Reverse transfer capacitance	C <sub>rss</sub>	f = 1.0 MHz, see	f = 1.0 MHz, see fig. 5		350	-	1
Total gate charge	Q <sub>g</sub>	V <sub>GS</sub> = 10 V		-	-	210	
Gate-source charge	Q <sub>gs</sub>			-	-	29	nC
Gate-drain charge	Q <sub>gd</sub>			-	-	110	1
Turn-on delay time	t <sub>d(on)</sub>	$V_{DD}$ = 250 V, $I_{D}$ = 20 A , $R_{G}$ = 4.3 $\Omega$ , $R_{D}$ = 13 $\Omega$ , see fig. 10 <sup>b</sup>		-	18	-	ns
Rise time	t <sub>r</sub>			-	59	-	
Turn-off delay time	t <sub>d(off)</sub>			-	110	-	
Fall time	t <sub>f</sub>			-	58	-	1
Internal drain inductance	L <sub>D</sub>	Between lead,	D. I	-	5.0	-	
Internal source inductance	L <sub>S</sub>	6 mm (0.25") from package and center of die contact		-	13	-	nH
<b>Drain-Source Body Diode Characteristic</b>	s						
Continuous source-drain diode current	Is	MOSFET symbol showing the integral reverse p - n junction diode		-	-	20	
Pulsed diode forward current <sup>a</sup>	I <sub>SM</sub>			-	-	80	А
Body diode voltage	$V_{SD}$	$T_{J} = 25  ^{\circ}\text{C},  I_{S} = 20  ^{\circ}$	20 A, V <sub>GS</sub> = 0 V <sup>b</sup>	-	-	1.8	V
Body diode reverse recovery time	t <sub>rr</sub>	T 05 °C 1 0	200 41/4+ 100 0/··-b	-	570	860	ns
Body diode reverse recovery charge	Q <sub>rr</sub>	$T_J = 25  ^{\circ}\text{C}, I_F = 20\text{A}, dI/dt = 100 A/µsb}$		-	5.7	8.6	μC
Forward turn-on time	t <sub>on</sub>	Intrinsic turn-on time is negligible (turn-on is dominated by L <sub>S</sub> and L <sub>D</sub>					

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)
- b. Pulse width  $\leq 300~\mu s;$  duty cycle  $\leq 2~\%$



# TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

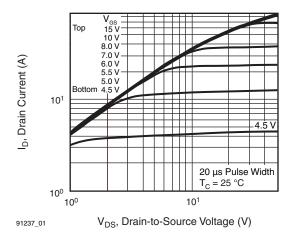


Fig. 1 - Typical Output Characteristics, T<sub>C</sub> = 25 °C

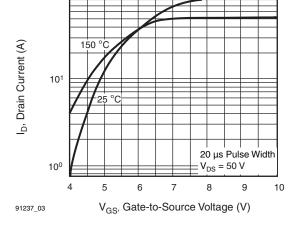


Fig. 3 - Typical Transfer Characteristics

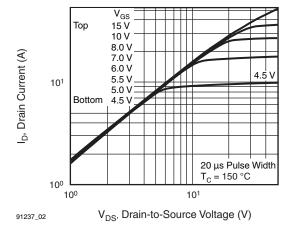


Fig. 2 - Typical Output Characteristics,  $T_C = 150$  °C

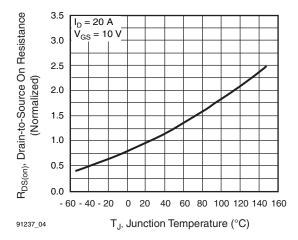


Fig. 4 - Normalized On-Resistance vs. Temperature



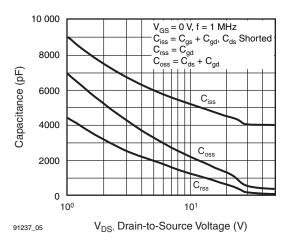


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

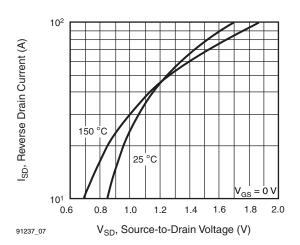


Fig. 7 - Typical Source-Drain Diode Forward Voltage

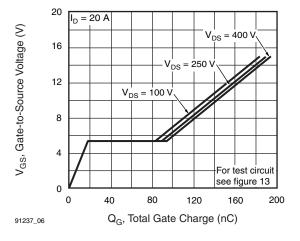


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

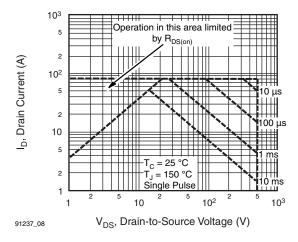


Fig. 8 - Maximum Safe Operating Area



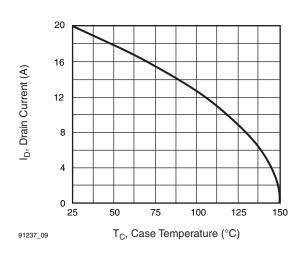


Fig. 9 - Maximum Drain Current vs. Case Temperature

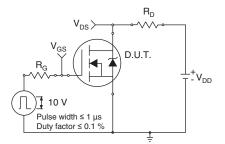


Fig. 10 - Switching Time Test Circuit

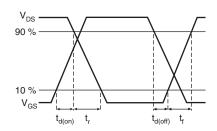


Fig. 11 - Switching Time Waveforms

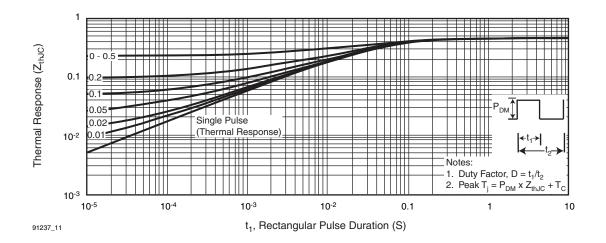


Fig. 12 - Maximum Effective Transient Thermal Impedance, Junction-to-Case



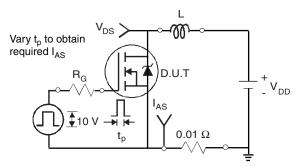


Fig. 13 - Unclamped Inductive Test Circuit

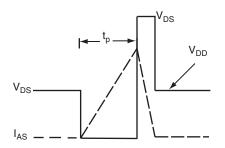


Fig. 14 - Unclamped Inductive Waveforms

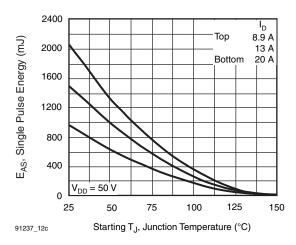


Fig. 15 - Maximum Avalanche Energy vs. Drain Current

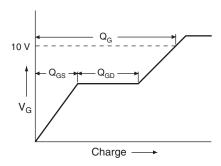


Fig. 16 - Basic Gate Charge Waveform

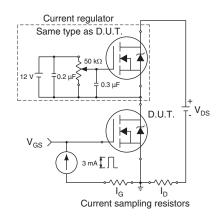
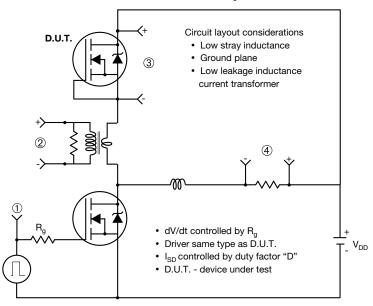


Fig. 17 - Gate Charge Test Circuit



### Peak Diode Recovery dV/dt Test Circuit



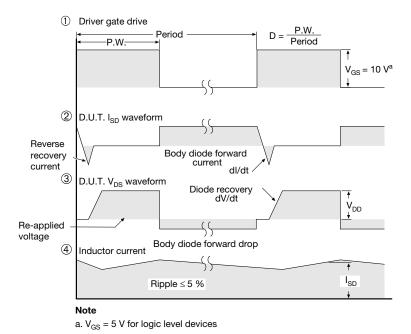


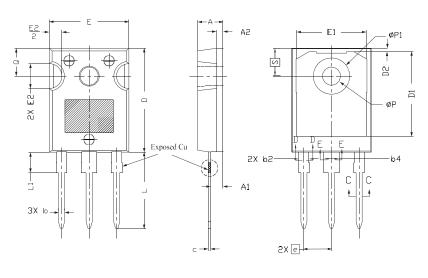
Fig. 18 - For N-Channel

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg?91237">www.vishay.com/ppg?91237</a>.

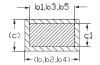


# **TO-247AC (High Voltage)**

### **VERSION 1: FACILITY CODE = 9**







Section C--C,D-D,E-E

	MILLIMETERS					
DIM.	MIN.	NOM.	MAX.	NOTES		
Α	4.83	5.02	5.21			
A1	2.29	2.41	2.55			
A2	1.17	1.27	1.37			
b	1.12	1.20	1.33			
b1	1.12	1.20	1.28			
b2	1.91	2.00	2.39	6		
b3	1.91	2.00	2.34			
b4	2.87	3.00	3.22	6, 8		
b5	2.87	3.00	3.18			
С	0.40	0.50	0.60	6		
c1	0.40	0.50	0.56			
D	20.40	20.55	20.70	4		

		MILLIMETERS	S	
DIM.	MIN.	NOM.	MAX.	NOTES
D1	16.46	16.76	17.06	5
D2	0.56	0.66	0.76	
E	15.50	15.70	15.87	4
E1	13.46	14.02	14.16	5
E2	4.52	4.91	5.49	3
е		5.46 BSC		
L	14.90	15.15	15.40	
L1	3.96	4.06	4.16	6
ØΡ	3.56	3.61	3.65	7
Ø P1	7.19 ref.			
Q	5.31	5.50	5.69	
S		5.51 BSC		

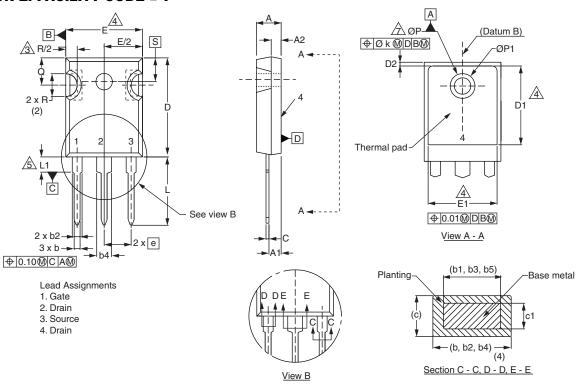
- (1) Package reference: JEDEC® TO247, variation AC
- (2) All dimensions are in mm
- (3) Slot required, notch may be rounded
- (4) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm per side. These dimensions are measured at the outermost extremes of the plastic body
- (5) Thermal pad contour optional with dimensions D1 and E1
- (6) Lead finish uncontrolled in L1
- $^{(7)}$  Ø P to have a maximum draft angle of 1.5° to the top of the part with a maximum hole diameter of 3.91 mm
- (8) Dimension b2 and b4 does not include dambar protrusion. Allowable dambar protrusion shall be 0.1 mm total in excess of b2 and b4 dimension at maximum material condition



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### **VERSION 2: FACILITY CODE = Y**



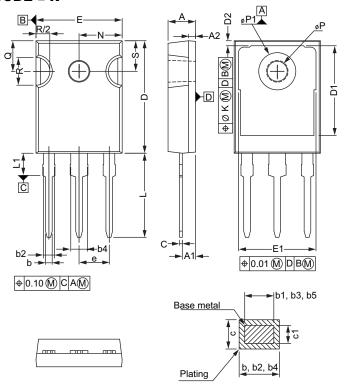
	MILLIM		
DIM.	MIN.	MAX.	NOTES
Α	4.58	5.31	
A1	2.21	2.59	
A2	1.17	2.49	
b	0.99	1.40	
b1	0.99	1.35	
b2	1.53	2.39	
b3	1.65	2.37	
b4	2.42	3.43	
b5	2.59	3.38	
С	0.38	0.86	
c1	0.38	0.76	
D	19.71	20.82	
D1	13.08	-	

	MILLIN		
DIM.	MIN.	MAX.	NOTES
D2	0.51	1.30	
Е	15.29	15.87	
E1	13.72	-	
е	5.46	BSC	
Øk	0.2	254	
L	14.20	16.25	
L1	3.71	4.29	
ØР	3.51	3.66	
Ø P1	-	7.39	
Q	5.31	5.69	
R	4.52	5.49	
S	5.51 BSC		

- (1) Dimensioning and tolerancing per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- (7) Outline conforms to JEDEC outline TO-247 with exception of dimension c



### **VERSION 3: FACILITY CODE = N**



	MILLIMETERS			
DIM.	MIN.	MAX.		
Α	4.65	5.31		
A1	2.21	2.59		
A2	1.17	1.37		
b	0.99	1.40		
b1	0.99	1.35		
b2	1.65	2.39		
b3	1.65	2.34		
b4	2.59	3.43		
b5	2.59	3.38		
С	0.38	0.89		
c1	0.38	0.84		
D	19.71	20.70		
D1	13.08	-		

	MILLIMETERS		
DIM.	MIN.	MAX.	
D2	0.51	1.35	
E	15.29	15.87	
E1	13.46	-	
е	5.46 BSC		
k	0.254		
L	14.20	16.10	
L1	3.71	4.29	
N	7.62	BSC	
Р	3.56	3.66	
P1	-	7.39	
Q	5.31	5.69	
R	4.52	5.49	
S	5.51	BSC	

ECN: E22-0452-Rev. G, 31-Oct-2022

DWG: 5971

- <sup>(1)</sup> Dimensioning and tolerancing per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")



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Vishay

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